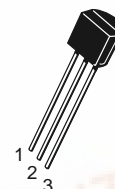
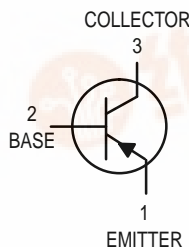


High Voltage Transistors

PNP Silicon

PBF493
PBF493S**CASE 29-04, STYLE 1**
TO-92 (TO-226AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-300	Vdc
Collector-Base Voltage	V_{CBO}	-300	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current — Continuous	I_C	-500	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage (1) ($I_C = -1.0$ mAdc, $I_E = 0$)	$V_{(BR)CEO}$	-300	—	Vdc
Collector-Base Breakdown Voltage ($I_C = -10$ μ Adc, $I_E = 0$)	$V_{(BR)CBO}$	-300	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = -100$ μ Adc, $I_C = 0$)	$V_{(BR)EBO}$	-5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = -200$ Vdc, $I_E = 0$)	I_{CBO}	—	-0.25	μ Adc
Emitter Cutoff Current ($V_{EB} = -3.0$ Vdc)	I_{EBO}	—	-20	nAdc
Collector Cutoff Current ($V_{CE} = -10$ Vdc)	I_{CEO}	—	-250	nAdc

1. Pulse Test: Pulse Width ≤ 300 μ s; Duty Cycle $\leq 2.0\%$.

PBF493 PBF493S**ELECTRICAL CHARACTERISTICS** ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
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ON CHARACTERISTICS

DC Current Gain ($I_C = -0.1\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -1.0\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$) ($I_C = -30\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$)	PBF493S All Types All Types	h_{FE}	40 40 25	— — —	—
Collector–Emitter Saturation Voltage ($I_C = -20\text{ mAdc}$, $I_B = -2.0\text{ mAdc}$)		$V_{CE(sat)}$	—	–0.5	Vdc
Base–Emitter Saturation Voltage ($I_C = -20\text{ mAdc}$, $I_B = -2.0\text{ mAdc}$)		$V_{BE(sat)}$	—	–0.9	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = -10\text{ mAdc}$, $V_{CE} = -20\text{ Vdc}$, $f = 20\text{ MHz}$)		f_T	50	—	MHz
Output Capacitance ($V_{CB} = -20\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)		C_{obo}	—	6.0	pF

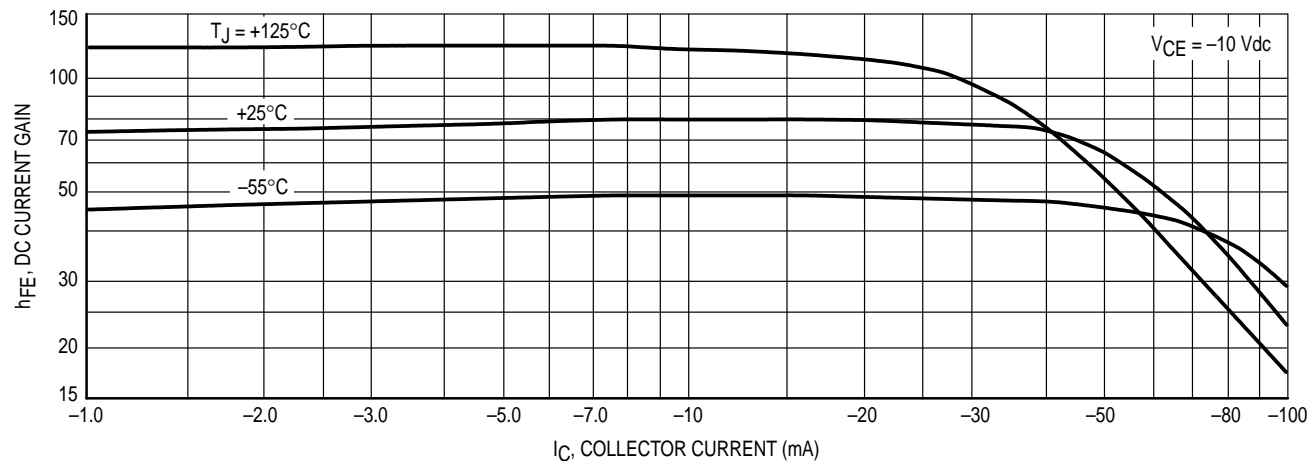


Figure 1. DC Current Gain

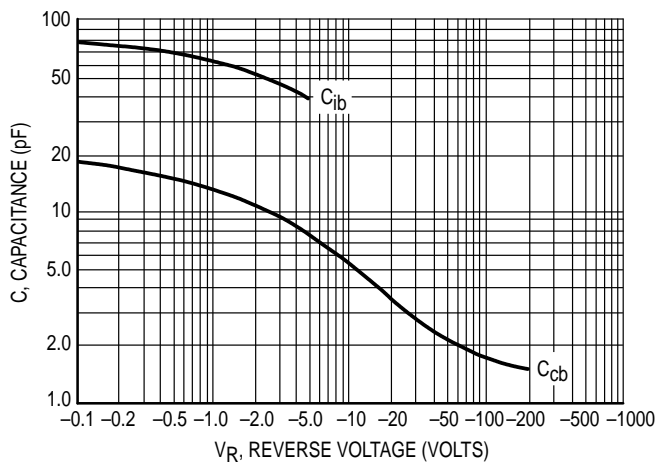


Figure 2. Capacitances

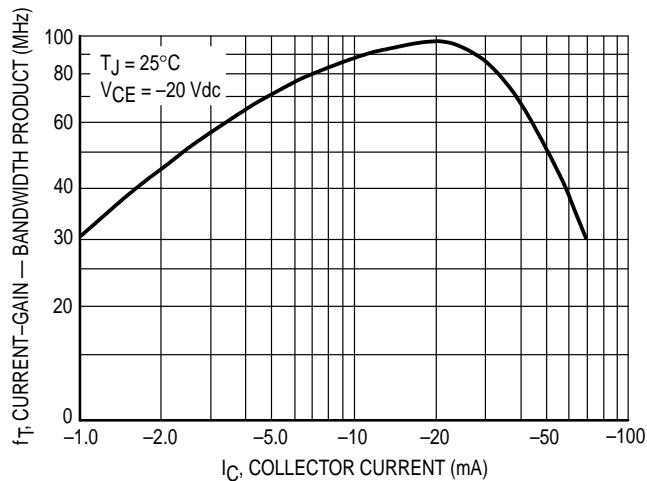


Figure 3. Current-Gain — Bandwidth Product

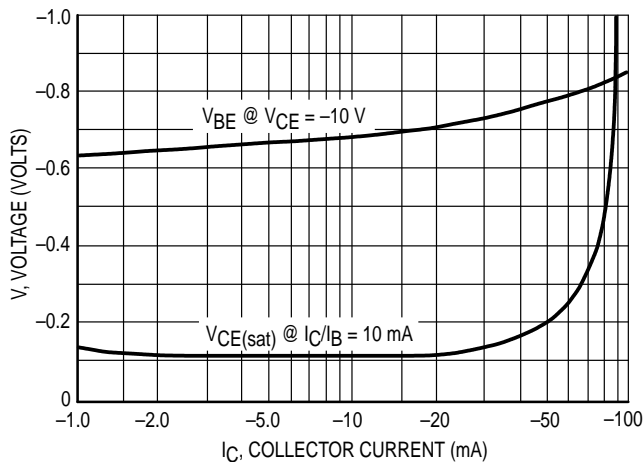


Figure 4. "On" Voltages

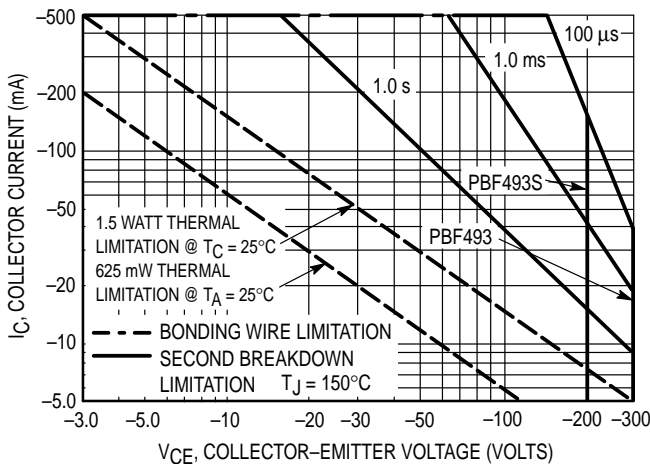
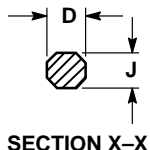
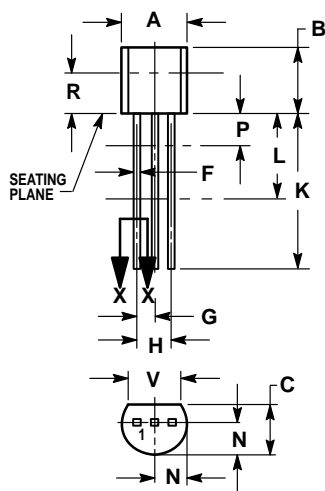


Figure 5. Active Region — Safe Operating Area

PACKAGE DIMENSIONS



**CASE 029-04
(TO-226AA)
ISSUE AD**


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

STYLE 1:

1. PIN 1. EMITTER
2. BASE
3. COLLECTOR

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How to reach us:

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution;
P.O. Box 20912, Phoenix, Arizona 85036. 1-800-441-2447 or 602-303-5454

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE 602-244-6609
INTERNET: <http://Design-NET.com>

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, 6F Seibu-Butsuryu-Center,
3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-81-3521-8315

ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

